

Junichi Murota

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Langmuir-Type Mechanism for In-Situ Doping in CVD Si and Si _{1-x} Ge _x Epitaxial Growth. ECS Journal of Solid State Science and Technology, 2021, 10, 024005.	1.8	2
2	Langmuir-Type Expressions for In-Situ Co-Doping of C with B or P in Si _{1-x} Ge _x Epitaxial Growth by Chemical Vapor Deposition. ECS Journal of Solid State Science and Technology, 2021, 10, 064004.	1.8	0
3	Langmuir-Type Mechanism for In-Situ Doping in CVD Silicon-Germanium Epitaxial Growth. ECS Transactions, 2019, 90, 43-53.	0.5	1
4	Langmuir-Type Mechanism for In-Situ Boron Doping in CVD Si _{1-x} Ge _x Epitaxial Growth. , 2018, , .		0
5	Atomically Controlled Processing for Dopant Segregation in CVD Si and Ge Epitaxial Growth. ECS Journal of Solid State Science and Technology, 2018, 7, P305-P310.	1.8	5
6	Arsenic atomic layer doping in Si using AsH ₃ . Solid-State Electronics, 2015, 110, 29-34.	1.4	7
7	Low-temperature reduction of Ge oxide by Si and SiH ₄ in low-pressure H ₂ and Ar environment. Solid-State Electronics, 2015, 110, 40-43.	1.4	2
8	Heavy carbon atomic-layer doping at Si _{1-x} Ge _x /Si heterointerface. Thin Solid Films, 2010, 518, S222-S225.	1.8	8
9	Heavy B atomic-layer doping characteristics in Si epitaxial growth on B adsorbed Si(1 0 0) by ultraclean low-pressure CVD system. Solid-State Electronics, 2009, 53, 877-879.	1.4	11
10	Si epitaxial growth on self-limitedly B adsorbed Si _{1-x} Ge _x (100) by ultraclean low-pressure CVD system. Thin Solid Films, 2008, 517, 229-231.	1.8	4
11	Carbon doping effect on strain relaxation during Si _{1-x} Ge _y epitaxial growth on Si(100) at 500 °C. Semiconductor Science and Technology, 2007, 22, S5-S8.	2.0	4
12	Epitaxial growth of P atomic layer doped Si film by alternate surface reactions of PH ₃ and Si ₂ H ₆ on strained Si _{1-x} Ge _x /Si(100) in ultraclean low-pressure CVD. Semiconductor Science and Technology, 2007, 22, S118-S122.	2.0	8
13	Atomically Controlled Processing for Group IV Semiconductors by Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2006, 45, 6767-6785.	1.5	84
14	Carbon effect on strain compensation in Si _{1-x} Ge _y films epitaxially grown on Si(100). Thin Solid Films, 2006, 508, 140-142.	1.8	7
15	Atomic layer processing for doping of SiGe. Thin Solid Films, 2006, 508, 279-283.	1.8	27
16	Effect of carbon on the thermal stability of a Si atomic layer on Ge(1 0 0). Applied Surface Science, 2004, 224, 206-209.	6.1	3
17	W delta doping in Si(1 0 0) using ultraclean low-pressure CVD. Applied Surface Science, 2003, 212-213, 684-688.	6.1	4
18	Phosphorus Doping in Si _{1-x} Ge _y Epitaxial Growth by Low-Pressure Chemical Vapor Deposition Using a SiH ₄ -GeH ₄ -CH ₃ SiH ₃ -PH ₃ -H ₂ Gas System. Japanese Journal of Applied Physics, 2001, 40, 2697-2700.	1.5	9

#	ARTICLE	IF	CITATIONS
19	Doping and electrical characteristics of in-situ heavily B-doped Si _{1-x} Ge _y films epitaxially grown using ultraclean LPCVD. Thin Solid Films, 2000, 380, 57-60.	1.8	23
20	Atomic-layer adsorption of P on Si(100) and Ge(100) by PH ₃ using an ultraclean low-pressure chemical vapor deposition. Applied Surface Science, 2000, 162-163, 390-394.	6.1	25
21	Doping and electrical characteristics of in situ heavily B-doped Si _{1-x} Ge _y films epitaxially grown using ultraclean LPCVD. Thin Solid Films, 1999, 343-344, 541-544.	1.8	15
22	Low-Temperature Epitaxial Growth of Si/Si _{1-x} Ge _x /Si Heterostructure by Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1994, 33, 2290-2299.	1.5	100
23	Self-limited layer-by-layer etching of Si by alternated chlorine adsorption and Ar ⁺ ion irradiation. Applied Physics Letters, 1993, 63, 2803-2805.	3.3	101
24	Electron-cyclotron resonance plasma-enhanced chemical vapor deposition of epitaxial Si without substrate heating by ultraclean processing. Applied Physics Letters, 1991, 59, 2853-2855.	3.3	32
25	Low-temperature silicon selective deposition and epitaxy on silicon using the thermal decomposition of silane under ultraclean environment. Applied Physics Letters, 1989, 54, 1007-1009.	3.3	106
26	Boron Doping Effect on Silicon Film Deposition in the Si ₂ H ₆ -C ₂ H ₂ B ₂ H ₆ -He Gas System. Electrochemical Society, 1986, 133, 1721-1724.	2.9	57
27	Selective Ge deposition on Si using thermal decomposition of GeH ₄ . Applied Physics Letters, 1985, 47, 863-865.	3.3	47
28	Deposition of Phosphorus Doped Silicon Films by Thermal Decomposition of Disilane. Japanese Journal of Applied Physics, 1984, 23, L493-L495.	1.5	30